

**PROGRAMMABLE MOS DEVICE FORMED BY STRESSING
POLYCRYSTALLINE SILICON**

ABSTRACT

[0033] A programmable memory circuit and a method for programming the same are disclosed. A polycrystalline silicon resistor pair are used in a programmable memory cell. The pair includes a first polycrystalline silicon resistor stressable by a predetermined current thereacross, and a second polycrystalline silicon resistor similarly structured as the first polycrystalline silicon resistor stressable by the predetermined current, wherein when only the first resistor is stressed by the predetermined current, a resistance of the first resistor is lowered as compared to the unstressed second resistor, thereby programming the memory cell.

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